

IN THE CLAIMS:

Please cancel claims 12, 16-20, 22-23, and 26-32 without prejudice, and amend the claims as follows:

1. (Previously Presented) An apparatus for processing a semiconductor substrate, comprising:

a chamber body having an internal volume defined by first and second substantially cylindrical regions and by side walls extending substantially tangent between the first and second substantially cylindrical regions;

a substrate support disposed in the internal volume within the first substantially cylindrical region; and

an exhaust system connected to a chamber outlet disposed in fluid communication with the second substantially cylindrical region.

2. (Previously Presented) The apparatus of claim 1, further comprising:

a chamber lid mounted on the chamber body; and

an electrode disposed on the chamber lid.

3. (Original) The apparatus of claim 2, wherein the electrode comprises one or more inductive coils.

4. (Original) The apparatus of claim 2, wherein the electrode comprises one or more flat coils.

5. (Previously Presented) An apparatus for processing a semiconductor substrate, comprising:

a chamber body having an internal volume defined by first and second substantially cylindrical regions and by side walls extending between the first and second substantially cylindrical regions,

a substrate support disposed in the internal volume within the first substantially cylindrical region;

an exhaust system connected to a chamber outlet disposed in fluid communication with the second substantially cylindrical region; and

one or more chamber liners defining a substantially cylindrical processing region adjacent the substrate support and an exhaust region adjacent the chamber outlet.

6. (Original) The apparatus of claim 5, wherein the substantially cylindrical processing region is in fluid communication with the exhaust region through a passage defined by the liner.

7. (Original) The apparatus of claim 6, wherein the liner further comprises a plasma confinement flange extending inwardly around the substrate support.

8. (Original) The apparatus of claim 7, wherein the substrate support further comprises a barrier flange surrounding the substrate support.

9. (Previously Presented) The apparatus of claim 5, wherein the first substantially cylindrical region has a first diameter at least 30% larger than a second diameter of the second substantially cylindrical region.

10. (Previously Presented) The apparatus of claim 5, wherein the first substantially cylindrical region has a first diameter at least 20% larger than a substrate support diameter.

11. (Currently Amended) An apparatus for processing a substrate, comprising:  
a chamber body having an internal volume, wherein the internal volume is defined by first and second substantially cylindrical regions and by straight side walls substantially tangent to the first and second substantially cylindrical regions;

one or more liners defining within the internal volume a substantially cylindrical processing region within the first substantially cylindrical region and a substantially

cylindrical exhaust region within the second substantially cylindrical region within the internal volume, wherein the substantially cylindrical processing region communicates with the substantially cylindrical exhaust region through one or more openings defined by the one or more liners;

a substrate support disposed in the substantially cylindrical processing region; and

an exhaust system in communication with the substantially cylindrical exhaust region through an exhaust port in the process chamber.

12. (Canceled)

13. (Currently Amended) The apparatus of claim 11 12, wherein the first substantially cylindrical region is parallel to the second substantially cylindrical region.

14. (Previously Presented) The apparatus of claim 13, wherein the first substantially cylindrical region has a first diameter at least 30% larger than a second diameter of the second substantially cylindrical region.

15. (Previously Presented) The apparatus of claim 13, wherein the first substantially cylindrical region has a first diameter at least 20% larger than a substrate support diameter.

16 -20. (Canceled)

21. (Currently Amended) An apparatus for processing a substrate, comprising:  
a chamber body comprising an internal volume and an exhaust port, wherein the internal volume is defined by at least first and second substantially cylindrical regions and by straight side walls substantially tangent to the first and second substantially cylindrical regions;

one or more liners defining an exhaust region and a processing region within the internal volume, wherein the exhaust region is co-axial with the exhaust port and the

processing region is on a parallel axis with the exhaust region, and wherein the one or more liners define the processing region in the first substantially cylindrical region and define the exhaust region in the second substantially cylindrical region; and  
a substrate support disposed in the processing region.

22.-23. (Canceled)

24. (Currently Amended) The apparatus of claim 21 23, wherein the first substantially cylindrical region has a first diameter at least 30% larger than a second diameter of the second cylindrical region.

25. (Currently Amended) The apparatus of claim 21 23, wherein the first substantially cylindrical region has a first diameter at least 20% larger than a substrate support diameter.

26-33. (Canceled)

34. (Previously Presented) The apparatus of claim 5, further comprising:  
a chamber lid mounted on the chamber body; and  
an electrode disposed on the chamber lid.

35. (Previously Presented) The apparatus of claim 34, wherein the electrode comprises one or more inductive coils.

36. (Previously Presented) The apparatus of claim 34, wherein the electrode comprises one or more flat coils.